

COMPAD

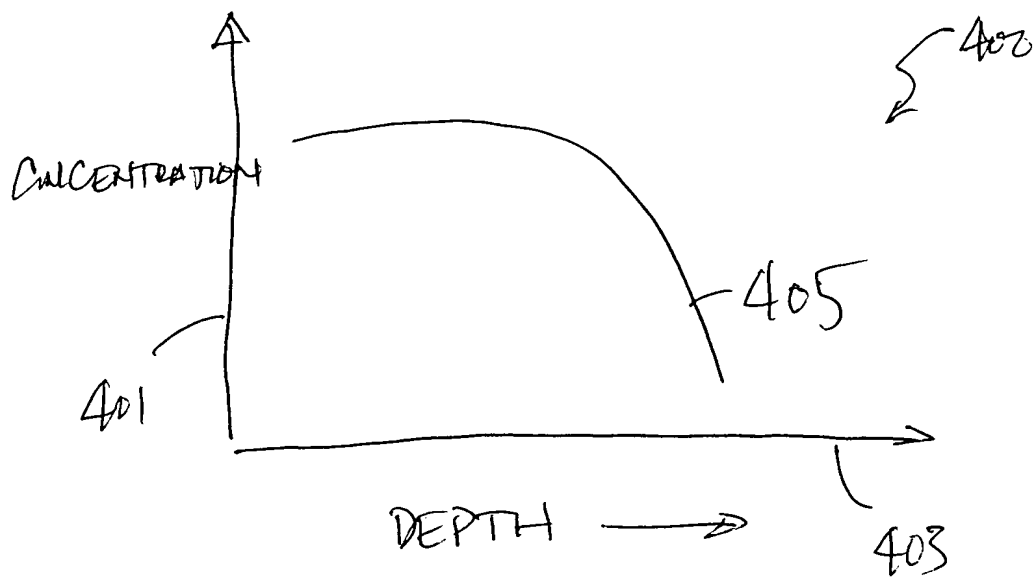


FIG. 4

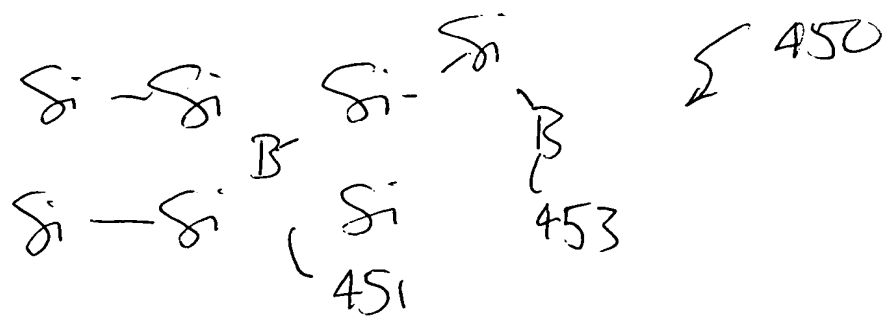


FIG. 4A

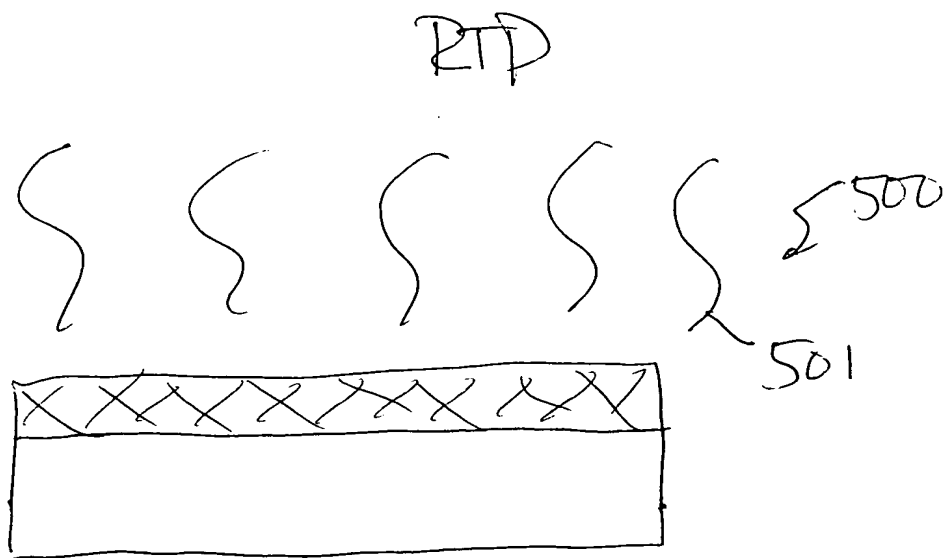


FIG. 5

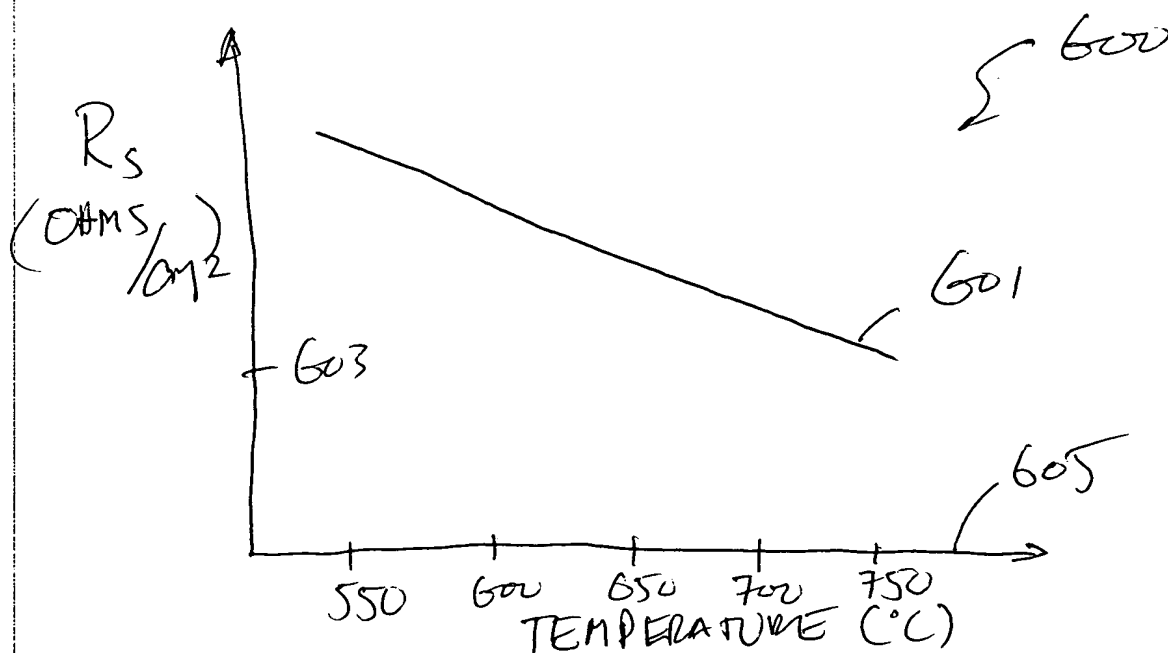
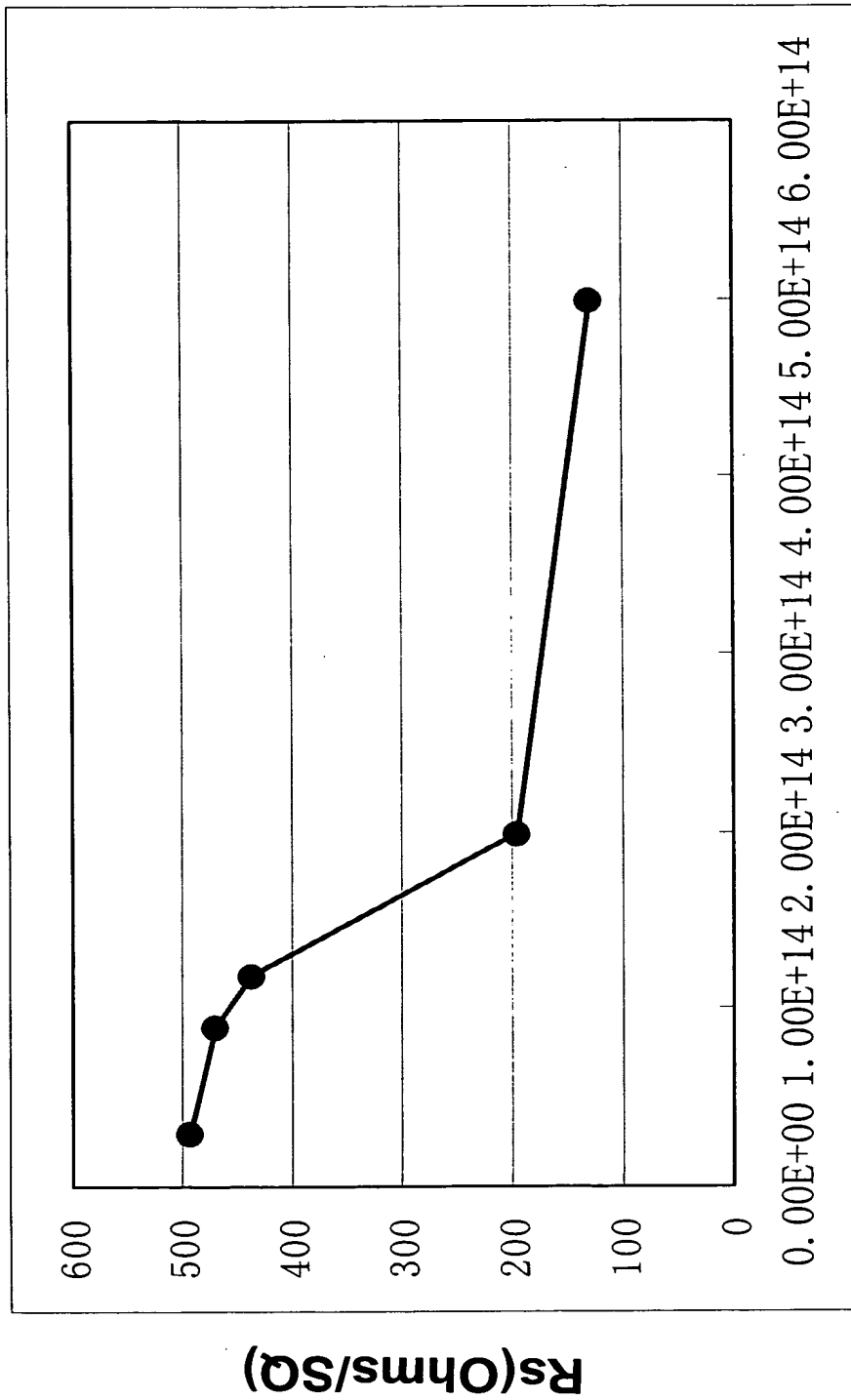


FIG. 6

Low temperature monitor



Dosage(atom/cm^2)

Figure 7: Changes of R_s as a function of implant dosage of silicon, Boron dosage unchanged($3.5\text{E}15$).

FIG. 7

Low temperature monitor

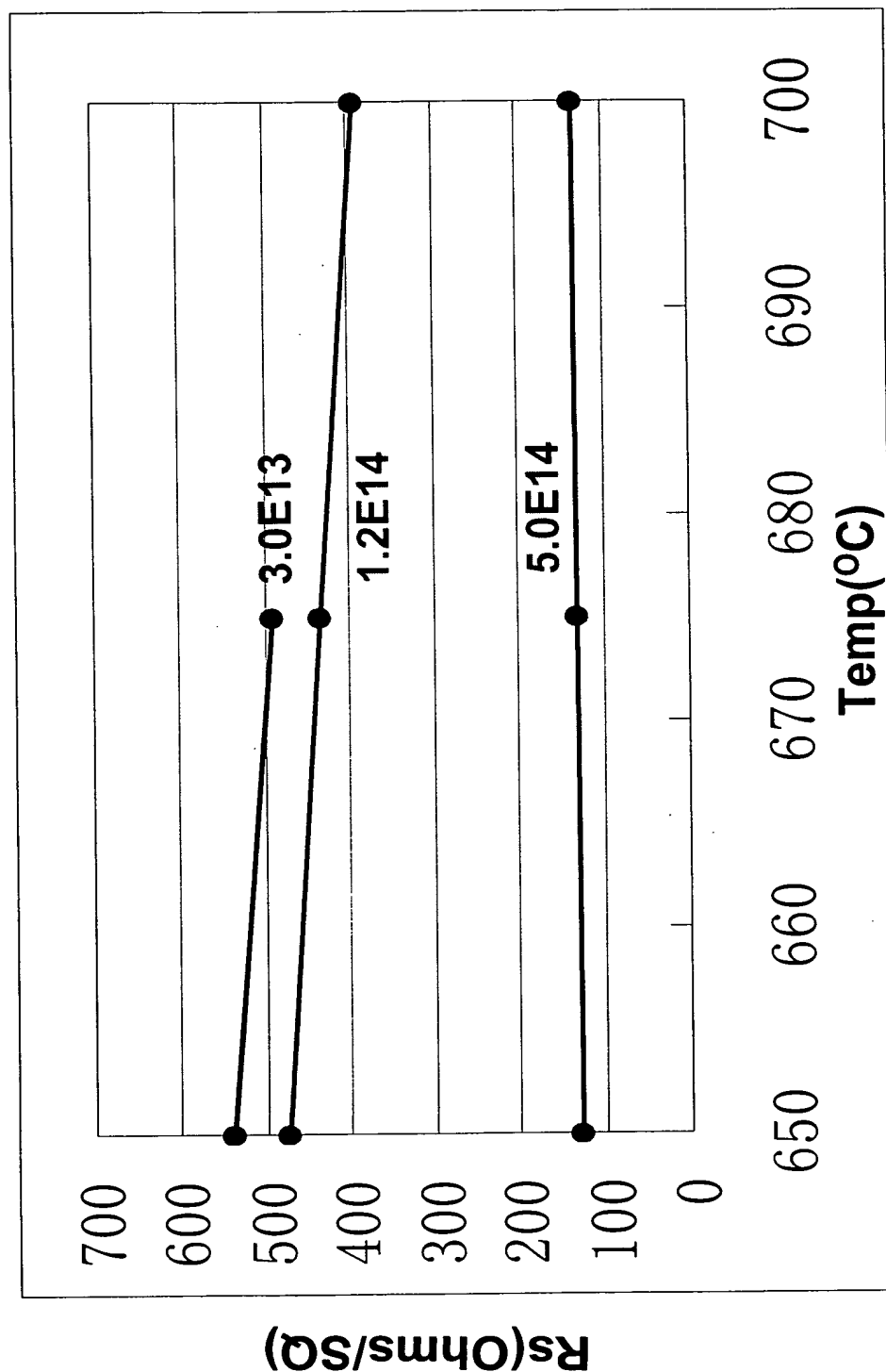


Figure 8: The dependence of R_s on annealing temperature. The implant dose of silicon varied from 3.0×10^{13} to 5.0×10^{14} , Boron dosage unchanged (3.5×10^{15}).

FIG. 8